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SEMICONDUCTOR



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PLED

B220-13-F(MS) THRU B2200B-13-F(MS)

Product specification




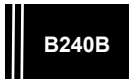






Features

- The plastic package carries Underwriters Laboratory Flammability Classification 94V-0
- For surface mounted applications
- Metal silicon junction, majority carrier conduction
- Low power loss, high efficiency
- Built-in strain relief, ideal for automated placement
- High forward surge current capability
- High temperature soldering guaranteed: 250°C/10 seconds at terminals

Mechanical Data

- **Case:** JEDEC DO-214AA molded plastic body
- **Terminals:** leads solderable per MIL-STD-750, Method 2026
- **Polarity:** Color band denotes cathode end
- **Mounting Position:** Any
- **Weight:** 0.003 ounce, 0.093 grams

Reference News

Outline	Marking		
			
	B220 -13-F(MS)	B230 -13-F(MS)	B240 -13-F(MS)
			
	B250 -13-F(MS)	B260 -13-F(MS)	B280 -13-F(MS)
			
	B2100-13-F(MS)	B2150-13-F(MS)	B2200-13-F(MS)
	SMB		

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

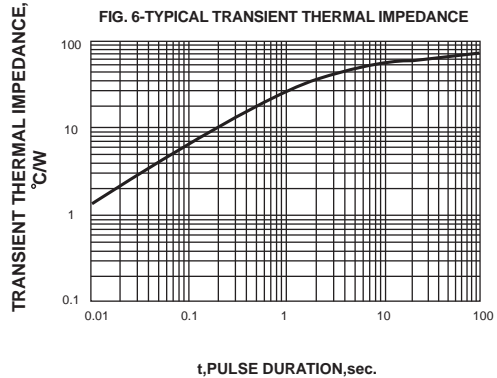
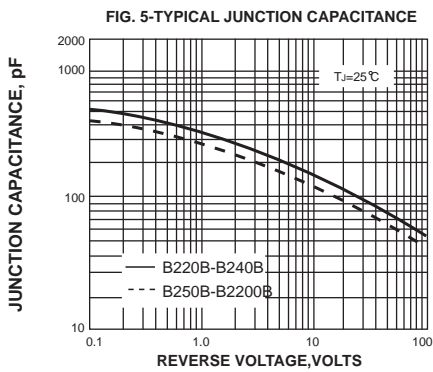
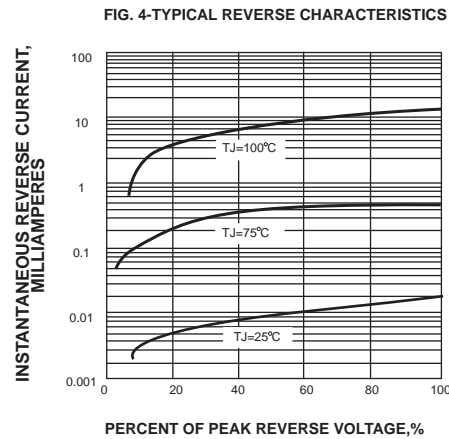
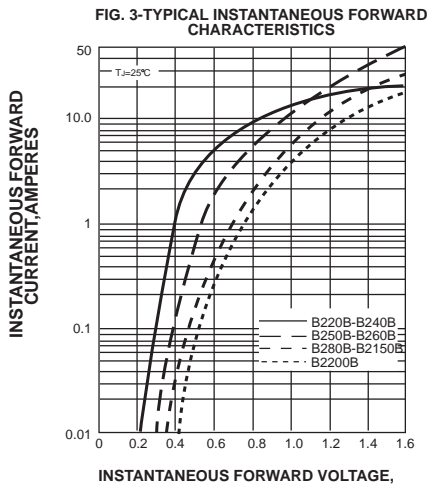
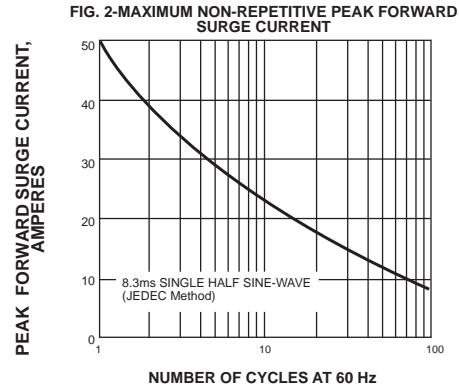
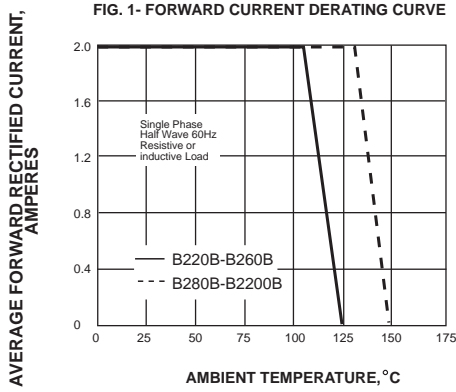
Ratings at 25°C ambient temperature unless otherwise specified.

Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

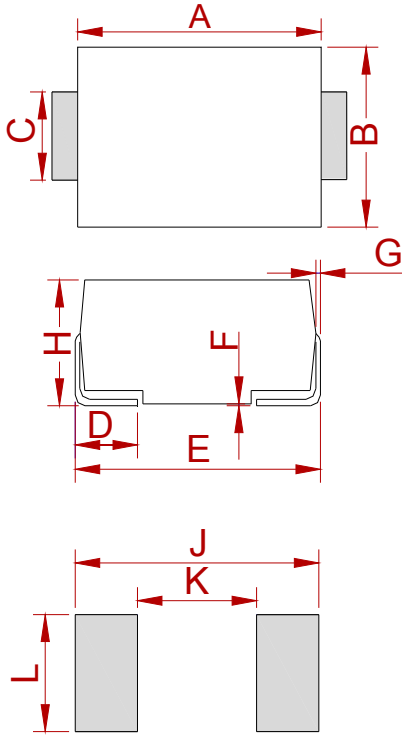
YFW Catalog Number	SYMBOLS	B220 -13-F(MS)	B230 -13-F(MS)	B240 -13-F(MS)	B250 -13-F(MS)	B260 -13-F(MS)	B280 -13-F(MS)	B2100 -13-F(MS)	B2150 -13-F(MS)	B2200 -13-F(MS)	UNITS
Maximum repetitive peak reverse voltage	V_{RRM}	20	30	40	50	60	80	100	150	200	VOLTS
Maximum RMS voltage	V_{RMS}	14	21	28	35	42	56	70	105	140	VOLTS
Maximum DC blocking voltage	V_{DC}	20	30	40	50	60	80	100	150	200	VOLTS
Maximum average forward rectified current at T_L (see fig.1)	I_{AV}	2.0									Amps
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	50.0									Amps
Maximum instantaneous forward voltage at 2.0A	V_F	0.55		0.70		0.85		0.95			Volts
Maximum DC reverse current at rated DC blocking voltage	I_R	0.5							0.2		mA
		10.0			5.0		2.0				
Typical junction capacitance (NOTE 1)	C_J	220			180					pF	
Typical thermal resistance (NOTE 2)	$R_{\theta JA}$	75.0									°C/W
Operating junction temperature range	T_J	-50 to +125					-50 to +150				°C
Storage temperature range	T_{STG}	-50 to +150									°C

Note: 1. Measured at 1MHz and applied reverse voltage of 4.0V D.C. 2.P.C.B. mounted with 0.2x0.2"(5.0x5.0mm) copper pad areas

RATINGS AND CHARACTERISTIC CURVES



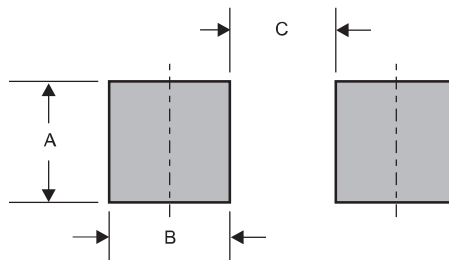
PACKAGE MECHANICAL DATA



DO-214AA (SMB)

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.25	4.75	0.167	0.187
B	3.30	3.94	0.130	0.155
C	1.85	2.21	0.073	0.087
D	0.76	1.52	0.030	0.060
E	5.08	5.59	0.200	0.220
F	0.051	0.203	0.002	0.008
G	0.15	0.31	0.006	0.012
H	2.11	2.44	0.083	0.096
J	6.80		0.270	
K		2.60		0.100
L	2.40		0.090	

Suggested solder pad layout



Dimensions in inches and (millimeters)

PACKAGE	A	B	C
SMB	0.078 (2.00)	0.059 (1.50)	0.110 (2.80)

REEL SPECIFICATION

P/N	PKG	QTY
B220-13-F(MS) THRU B2200B-13-F(MS)	SMB	3000

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